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Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

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Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China









Pch -30V -4A Power MOSFET

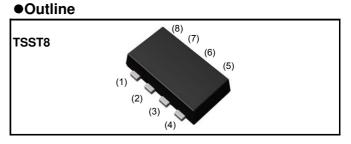
V_{DSS}	-30V
R _{DS(on)} (Max.)	45m $Ω$
I _D	-4A
P_D	1.25W

Features

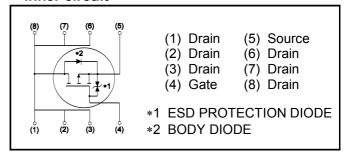
- 1) Low on resistance.
- 2) Built-in G-S Protection Diode.
- 3) Small Surface Mount Package (TSST8).
- 4) Pb-free lead plating; RoHS compliant

Application

DC/DC converters



•Inner circuit



Packaging specifications

	Packaging	Taping
Туре	Reel size (mm)	180
	Tape width (mm)	8
	Basic ordering unit (pcs)	3,000
	Taping code	TR
	Marking	UG

● Absolute maximum ratings(T_a = 25°C)

Parameter	Symbol	Value	Unit
Drain - Source voltage	$V_{ extsf{DSS}}$	-30	V
Continuous drain current	I _D *1	<u>+</u> 4	А
Pulsed drain current	I _{D,pulse} *2	±16	А
Gate - Source voltage	V_{GSS}	±20	V
Dower discination	P _D *3	1.25	W
Power dissipation	P _D *4	0.55	W
Junction temperature	T _j	150	°C
Range of storage temperature	T _{stg}	−55 to +150	°C

●Thermal resistance

Parameter	Symbol	Values			Unit
- Faranietei	Зушьог	Min.	Тур.	Max.	Offic
Thermal resistance, junction - ambient	R _{thJA} *3	-	-	100	°C/W
	R _{thJA} *4	1	1	227	°C/W

•Electrical characteristics($T_a = 25$ °C)

Parameter	Symbol	Conditions	Values			Unit
r ai ai ii etei	Symbol	Conditions	Min.	Тур.	Max.	Offic
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V$, $I_D = -1mA$	-30	-	-	V
Breakdown voltage temperature coefficient	$\frac{\Delta V_{(BR)DSS}}{\Delta T_{j}}$	I _D = -1mA referenced to 25°C	1	-25	-	mV/°C
Zero gate voltage drain current	I _{DSS}	$V_{DS} = -30V, V_{GS} = 0V$	ı	1	-1	μΑ
Gate - Source leakage current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$	1	1	±10	μΑ
Gate threshold voltage	V _{GS (th)}	$V_{DS} = -10V, I_{D} = -1mA$	-1	ı	-2.5	V
Gate threshold voltage temperature coefficient	$\frac{\Delta V_{(GS)th}}{\Delta T_{j}}$	I _D = -1mA referenced to 25°C	ı	3.9	-	mV/°C
		$V_{GS} = -10V, I_D = -4A$	-	32	45	
Static drain - source	D *5	$V_{GS} = -4.5V, I_{D} = -2A$	ı	45	63	mΩ
on - state resistance	$R_{DS(on)}^{-5}$	$V_{GS} = -4.0V, I_{D} = -2A$	ı	52	72	11122
		V _{GS} = -10V, I _D = -4A, T _j =125°C	ı	47	66	
Gate input resistannce	R_{G}	f = 1MHz, open drain	-	13	-	Ω
Transconductance	9 _{fs} *5	$V_{DS} = -10V, I_{D} = -4A$	2.7	7.0	-	S

^{*1} Limited only by maximum temperature allowed.

^{*2} Pw \leq 10 $\mu s,~Duty~cycle \leq$ 1%

^{*3} Mounted on a ceramic board (30×30×0.8mm)

^{*4} Mounted on a FR4 (20×20×0.8mm)

^{*5} Pulsed

• Electrical characteristics ($T_a = 25$ °C)

Parameter	Symbol	Conditions	Values			Unit	
- Farameter	Symbol Conditions –		Min.	Тур.	Max.	Offic	
Input capacitance	C _{iss}	V _{GS} = 0V	-	1000	-		
Output capacitance	C _{oss}	V _{DS} = -10V	-	150	-	pF	
Reverse transfer capacitance	C_{rss}	f = 1MHz	-	130	-		
Turn - on delay time	t _{d(on)} *5	$V_{DD} \simeq -15V$, $V_{GS} = -10V$	-	15	-		
Rise time	t _r *5	$I_D = -2A$	-	30	-	no	
Turn - off delay time	t _{d(off)} *5	$R_L = 7.5\Omega$	-	85	-	ns	
Fall time	t _f *5	$R_G = 10\Omega$	-	45	-		

•Gate Charge characteristics($T_a = 25$ °C)

Parameter	Cumbal	Conditions	Values			Unit
- Farameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Total gate charge	Q_{g}^{*5}	$V_{DD} \simeq -15V$, $I_D = -9A$ $V_{GS} = -5V$	-	10.5	-	
Total gate charge		$V_{DD}^{\sim} -15V, I_{D} = -4A$ $V_{GS} = -10V$	-	20	-	nC
Gate - Source charge	Q _{gs} *5	$V_{DD}^{\sim} -15V$, $I_D = -4A$ $V_{GS} = -5V$	-	3.0	-	
Gate - Drain charge	Q _{gd} *5	$V_{GS} = -5V$	-	3.3	-	

●Body diode electrical characteristics (Source-Drain)(T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
r ai ai ii etei	Symbol		Min.	Тур.	Max.	Offic
Inverse diode continuous, forward current	l _S *1	T _a = 25°C	-	-	-1	Α
Forward voltage	V _{SD} *5	$V_{GS} = 0V$, $I_s = -4A$	-	-	-1.2	V

• Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

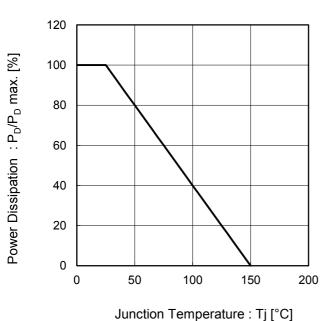
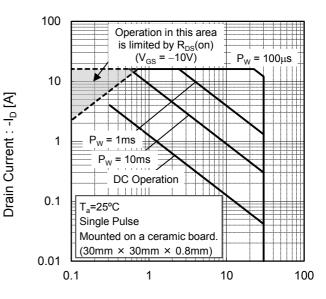
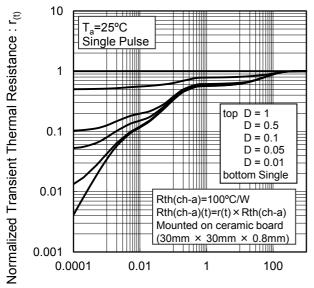


Fig.2 Maximum Safe Operating Area



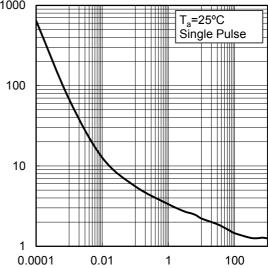
Drain - Source Voltage : -V_{DS} [V]

Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width



Pulse Width: Pw [s]

Fig.4 Single Pulse Maxmum Power dissipation 1000 T_a=25°C



Pulse Width : P_W [s]

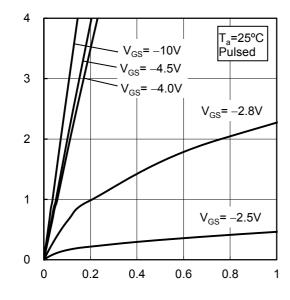
Peak Transient Power: P(W)

Drain Current: -I_D [A]

Drain - Source Breakdown Voltage : -V_{(BR)DSS} [V]

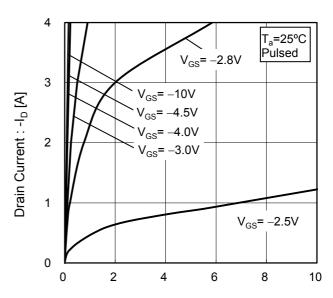
• Electrical characteristic curves

Fig.5 Typical Output Characteristics(I)



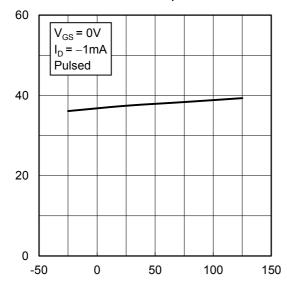
Drain - Source Voltage : -V_{DS} [V]

Fig.6 Typical Output Characteristics(II)



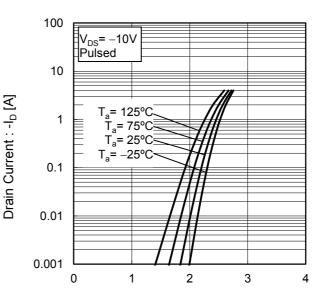
Drain - Source Voltage : -V_{DS} [V]

Fig.7 Breakdown Voltage vs. Junction Temperature



Junction Temperature : T_j [°C]

Fig.8 Typical Transfer Characteristics



Gate - Source Voltage : -V_{GS} [V]

Gate Threshold Voltage : - $V_{GS(th)}[V]$

• Electrical characteristic curves

Fig.9 Gate Threshold Voltage vs. Junction Temperature

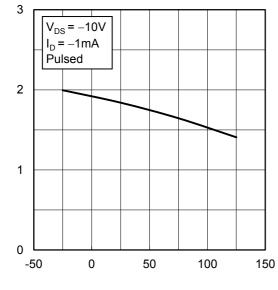
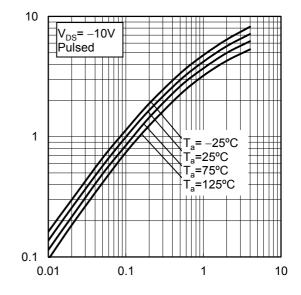


Fig.10 Transconductance vs. Drain Current



Junction Temperature : T_i [°C] Drain Current : $-I_D$ [A]

Transconductance: g_{fs} [S]

Fig.11 Drain CurrentDerating Curve

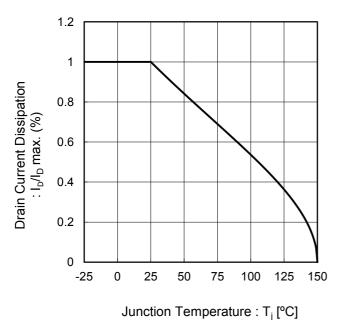
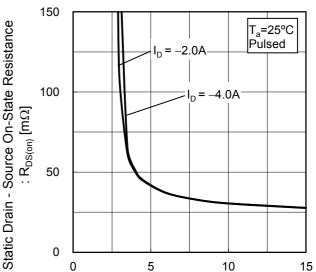


Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage



Gate - Source Voltage : -V_{GS} [V]

• Electrical characteristic curves

Resistance vs. Drain Current(I)

Ta=25°C
Pulsed

VGS=-4.0V
VGS=-4.5V
VGS=-10V

VGS=-10V

Ta=25°C
Ta=25

Drain Current: -ID [A]

Fig.13 Static Drain - Source On - State

Fig.14 Static Drain - Source On - State Resistance vs. Junction Temperature 50 Static Drain - Source On-State Resistance 40 30 $:R_{\text{DS(on)}}\left[m\Omega \right]$ 20 $V_{GS} = -10V$ $I_{D} = -2.0A$ 10 Pulsed 0 -25 0 25 50 75 100 125 150 -50 Junction Temperature : T_i [°C]

Fig. 15 Static Drain - Source On - State Resistance vs. Drain Current(II)

1000

V_{GS} = -10V
Pulsed

T_a = 125°C
T_a = 75°C
T_a = 25°C
T_a = -25°C

T_a = -25°C

T_a = 100

Drain Current : -I_D [A]

Resistance vs. Drain Current(III)

1000 $V_{GS} = -4.5V$ Pulsed $V_{GS} = -4.5V$ Pulsed $V_{GS} = -4.5V$ $V_{GS} = -4.5V$

Fig.16 Static Drain-Source On-State

• Electrical characteristic curves

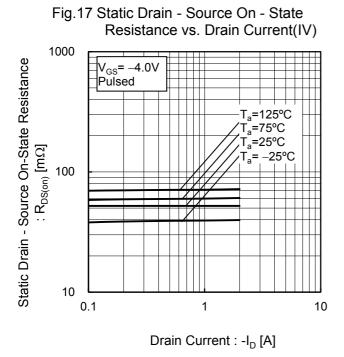
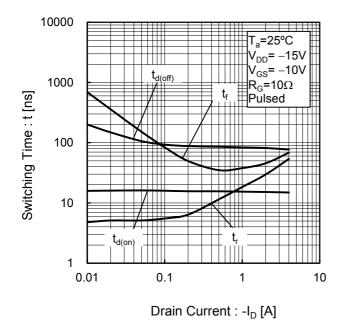


Fig. 18 Typical Capacitance vs. Drain - Source Voltage $\begin{array}{c}
10000 \\
T_a = 25^{\circ}C \\
f = 1MHz \\
V_{GS} = 0V
\end{array}$ 1000 $\begin{array}{c}
C_{iss} \\
C_{oss}
\end{array}$ 1000 $\begin{array}{c}
C_{rss} \\
0.01 \\
0.01 \\
0.1 \\
10
\end{array}$ 100

Fig.19 Switching Characteristics



Gate - Source Voltage : - V_{GS} [V]

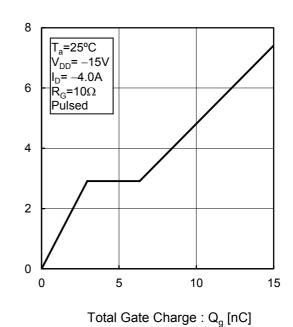
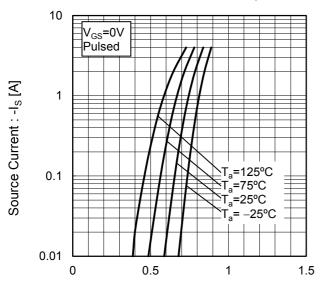


Fig.20 Dynamic Input Characteristics

Drain - Source Voltage : -V_{DS} [V]

•Electrical characteristic curves

Fig.21 Source Current vs. Source Drain Voltage



Source-Drain Voltage : - V_{SD} [V]

● Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

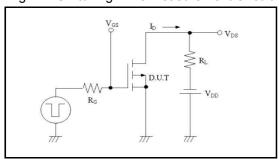


Fig.2-1 Gate Charge Measurement Circuit

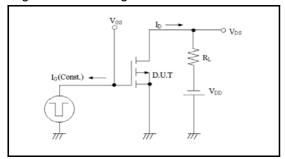


Fig.1-2 Switching Waveforms

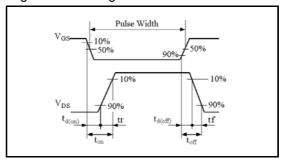
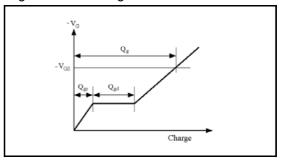
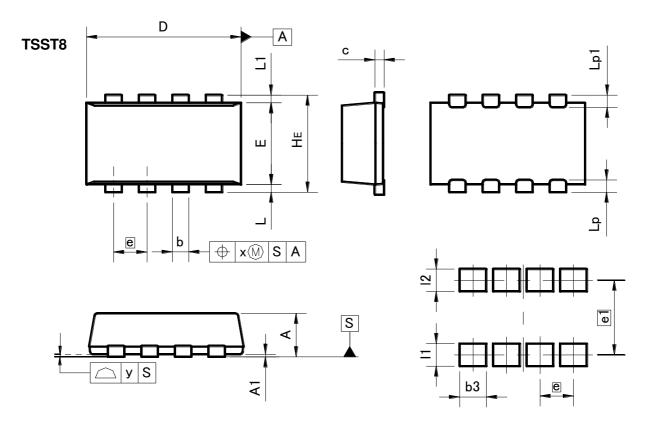


Fig.2-2 Gate Charge Waveform



●Dimensions (Unit: mm)



Patterm of terminal position areas

DIM	MILIM	ETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	0.75	0.85	0.03	0.033	
A1	0.00	0.05	0	0.002	
b	0.22	0.42	0.009	0.017	
С	0.12	0.22	0.005	0.009	
D	2.90	3.10	0.114	0.122	
E	1.50	1.70	0.059	0.067	
е	0.0	65	0.03		
HE	1.80	2.00	0.071	0.079	
L	0.05	0.25	0.002	0.01	
L1	0.05	0.25	0.002	0.01	
Lp	0.15	0.34	0.006	0.013	
Lp1	0.15	0.34	0.006	0.013	
Х	_	0.10		0.004	
У	_	0.10		0.004	

DIM	MILIM	MILIMETERS		HES
DIM	MIN	MAX	MIN	MAX
e1	1.46 0.06			06
b3	_	0.52	_	0.02
l1	_	0.44	_	0.017
12	_	0.44	_	0.017

Dimension in mm/inches

Notes

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